

What is claimed is:

1. A light-emitting device comprising:
a first passivation film and a second passivation film; and
5 a light-emitting element formed between the first passivation film and the second passivation film,
wherein the light-emitting element comprises an anode, a cathode and a light-emitting layer between the anode and the cathode;
wherein the light-emitting layer comprises a dopant at a concentration of
10 0.1 % by weight or more and 0.4 % by weight or less.
2. A light-emitting device comprising:
a first passivation film and a second passivation film;
a photosensitive organic resin film having an opening; and
15 a light-emitting element having an anode, a cathode and a light-emitting layer between the anode and the cathode,
wherein the light-emitting layer comprises a dopant at a concentration of 0.1 % by weight or more and 0.4 % by weight or less;
wherein the anode and the photosensitive organic resin film are formed on
20 the first passivation film;
wherein the anode, the cathode and the light-emitting layer are overlapped in the opening,
wherein the photosensitive organic resin film and the cathode are covered with the second passivation film.
- 25 3. A light-emitting device according to claim 2, wherein a radius of curvature of a curve that a section in the opening of the photosensitive organic resin film depicts is in the range of from 0.2 to 2 μm .
- 30 4. A light-emitting device according to claim 2, wherein the photosensitive

organic resin film has positive photosensitivity.

5. A light-emitting device according to claim 2, wherein the photosensitive organic resin film has negative photosensitivity.

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6. A light-emitting device according to any one of claims 1 and 2, wherein at least one of the first passivation film and the second passivation film is a carbon nitride film or a silicon nitride film formed by an RF sputtering process.

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7. A light-emitting device according to any one of claims 1 and 2, wherein at least one of the first passivation film and the second passivation film comprises a material selected from the group consisting of DLC, boron nitride and alumina.

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8. A light-emitting device as according to any one of claim 1 and 2, wherein the light-emitting device includes a transistor that controls a current that is supplied to the light-emitting element, and wherein the transistor is operated in a saturation region.

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9. A light-emitting device according to any one of claims 1 and 2, wherein the light-emitting element, after turning on for 100 hr with an initial intrinsic brightness set at 320 cd/mm^2 and a duty ratio set at 70 %, has a diminishing amount of the intrinsic brightness of substantially 10 % or less of the initial intrinsic brightness.

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10. A light-emitting device according to any one of claims 1 and 2, wherein the light-emitting element, after turning on for 1000 hr with an initial intrinsic brightness set at 320 cd/mm^2 and a duty ratio set at 70 %, has a diminishing amount of the intrinsic brightness of substantially 20 % or less of the initial intrinsic brightness.

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11. A light-emitting device according to any one of claims 1 and 2,
wherein the light-emitting device includes a transistor that controls a current
that is supplied to the light-emitting element,
wherein both the light-emitting element and the transistor are plurally
5 disposed in a pixel portion of the light-emitting device,
wherein the pixel portion is disposed on a substrate, and
wherein when brightness of the light-emitting element is set at 200 nt when a
duty ratio is set at 70 %, a temperature of a portion that overlaps with the pixel portion
of the substrate is 40 degree centigrade or less.

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12. A light-emitting device according to any one of claims 1 and 2,
wherein the light-emitting device includes a transistor that controls a current
that is supplied to the light-emitting element,
wherein both the light-emitting element and the transistor are plurally
15 disposed in a pixel portion of the light-emitting device,
wherein the pixel portion is disposed on a substrate,
wherein when power consumption of the light-emitting element and the
transistor is set at 600 mW when a duty ratio is set at 70 %, a temperature of a portion
that overlaps with the pixel portion of the substrate is 40 degree centigrade or less.

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13. A light-emitting device as set forth in any one of claims 1 through 8:
wherein the light-emitting device includes a transistor that controls a current
that is supplied to the light-emitting element;
both the light-emitting element and the transistor are plurally disposed in a
25 pixel portion of the light-emitting device; and
the pixel portion is disposed on a substrate;
wherein when brightness of the light-emitting element is set at 130 nt when a
duty ratio is set at 70 %, a temperature of a portion that overlaps with the pixel portion
of the substrate is 35 degree centigrade or less.

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14. A light-emitting device according to any one of claims 1 and 2,
wherein the light-emitting device includes a transistor that controls a current
that is supplied to the light-emitting element,

wherein both the light-emitting element and the transistor are plurally
5 disposed in a pixel portion of the light-emitting device,

wherein the pixel portion is disposed on a substrate, and

wherein when power consumption of the light-emitting element and the
transistor is set at 400 mW when a duty ratio is set at 70 %, a temperature of a portion
that overlaps with the pixel portion of the substrate is 35 degree centigrade or less.

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15. A light-emitting device according to any one of claims 1 and 2, wherein
the light-emitting layer comprises a quinacridone derivative.

16. A method of manufacturing a light-emitting device that includes an
15 anode, a cathode and a light-emitting element disposed between the anode and the
cathode, comprising:

forming the anode on a first passivation film;

forming a photosensitive organic resin film over the anode;

forming an opening partially in the photosensitive organic resin film by
20 exposure so that the anode is partially exposed;

heating the organic resin film under a vacuum atmosphere;

forming a light-emitting layer having a dopant concentration of 0.1 % by
weight or more and 0.4 % by weight or less over the organic resin film and the anode;

forming the cathode over the light-emitting layer so that the anode, the
25 cathode and the light-emitting layer are overlapped in the opening; and

forming a second passivation film over the organic resin film and the
cathode.

17. A method of manufacturing a light-emitting device according to claim
30 16, wherein the vacuum atmosphere is a vacuum of 3×10^{-7} Torr or less.

18. A method of manufacturing a light-emitting device according to claim 16, wherein at least one of the first passivation film and the second passivation film is a carbon nitride film or a silicon nitride film deposited by an RF sputtering process.

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19. A method of manufacturing a light-emitting device according to claim 16, wherein at least one of the first passivation film and the second passivation film comprises a material selected from the group consisting of DLC, boron nitride and alumina.

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20. A method of manufacturing a light-emitting device according to claim 16, wherein a radius of curvature of a curve that a section in the opening of the organic resin film depicts is in the range of from 0.2 to 2 μm .

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21. A method of manufacturing a light-emitting device according to claim 16, wherein the organic resin film has positive photosensitivity.

22. A method of manufacturing a light-emitting device according to claim 16, wherein the organic resin film has negative photosensitivity.

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